



Description

JMT N-channel Enhancement Mode Power MOSFET

Features

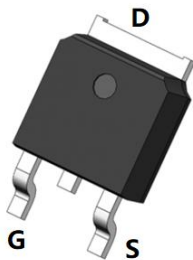
- 100V,59A
 $R_{DS(ON)} < 20m\Omega @ V_{GS} = 10V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

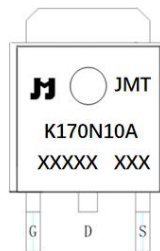
- Load Switch
- PWM Application
- Power management



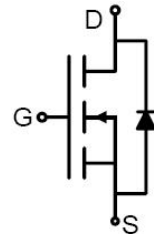
100% UIS TESTED!
100% ΔVds TESTED!



TO-252-4R(DPAK) top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | OUTLINE | Device Package | TUBE (PCS) | Inner BOX (PCS) | Per Carton (PCS) |
|----------------|-------------|---------|----------------|------------|-----------------|------------------|
| JMTK170N10A | JMTK170N10A | TAPING | TO-252-4R | 13inch | 2500 | 25000 |

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise specified)

| Symbol | Parameter | Max. | Units |
|-----------------|---|---------------------|--------------|
| V_{DSS} | Drain-Source Voltage | 100 | V |
| V_{GSS} | Gate-Source Voltage | ± 25 | V |
| I_D | Continuous Drain Current | $T_C = 25^\circ C$ | 59 |
| | | $T_C = 100^\circ C$ | 38 |
| I_{DM} | Pulsed Drain Current ^{note1} | 236 | A |
| E_{AS} | Single Pulsed Avalanche Energy ^{note2} | 98 | mJ |
| P_D | Power Dissipation | $T_C = 25^\circ C$ | 153 |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 0.98 | $^\circ C/W$ |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +175 | $^\circ C$ |



Electrical Characteristics (T_C=25°C unless otherwise specified)

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|---|---|---|------|------|------|-------|
| Off Characteristic | | | | | | |
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250μA | 100 | - | - | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =100V, V _{GS} =0V, | - | - | 1.0 | μA |
| I _{GSS} | Gate to Body Leakage Current | V _{DS} =0V, V _{GS} =±25V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250μA | 2 | 3 | 4 | V |
| R _{DS(on)} | Static Drain-Source on-Resistance <small>note3</small> | V _{GS} =10V, I _D =30A | - | 15 | 20 | mΩ |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} =25V, V _{GS} =0V, f=1.0MHz | - | 5211 | - | pF |
| C _{oss} | Output Capacitance | | - | 232 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | | - | 163 | - | pF |
| Q _g | Total Gate Charge | V _{DS} =30V, I _D =30A, V _{GS} =10V | - | 94 | - | nC |
| Q _{gs} | Gate-Source Charge | | - | 16 | - | nC |
| Q _{gd} | Gate-Drain("Miller") Charge | | - | 24 | - | nC |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-on Delay Time | V _{DS} =30V, I _D =2A, R _L =15Ω, R _{GEN} =2.5Ω, V _{GS} =10V | - | 15 | - | ns |
| t _r | Turn-on Rise Time | | - | 11 | - | ns |
| t _{d(off)} | Turn-off Delay Time | | - | 52 | - | ns |
| t _f | Turn-off Fall Time | | - | 13 | - | ns |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| I _S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | 59 | A |
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 236 | A |
| V _{SD} | Drain to Source Diode Forward Voltage | V _{GS} =0V, I _S =59A | - | - | 1.2 | V |
| trr | Body Diode Reverse Recovery Time | T _J = 25°C I _F =28A, di/dt=100A/μs | - | 33 | - | ns |
| Qrr | Body Diode Reverse Recovery Charge | | - | 54 | - | nC |

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
 2. EAS condition: T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω, I_{AS}=19.8A
 3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

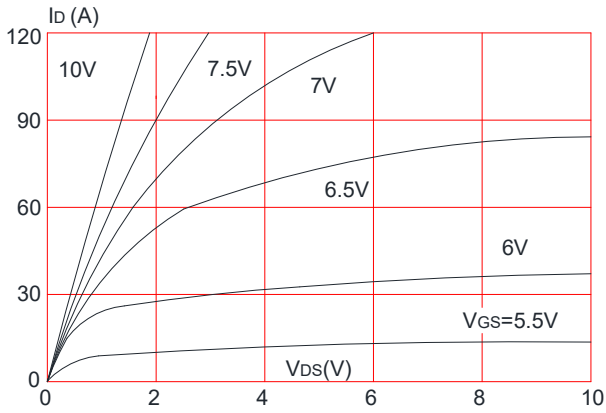


Figure 2: Typical Transfer Characteristics

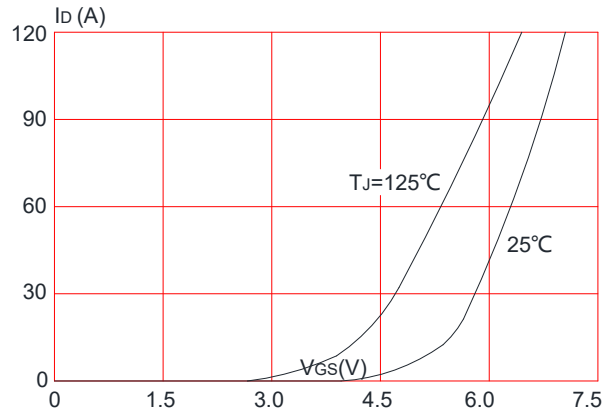


Figure 3: On-resistance vs. Drain Current

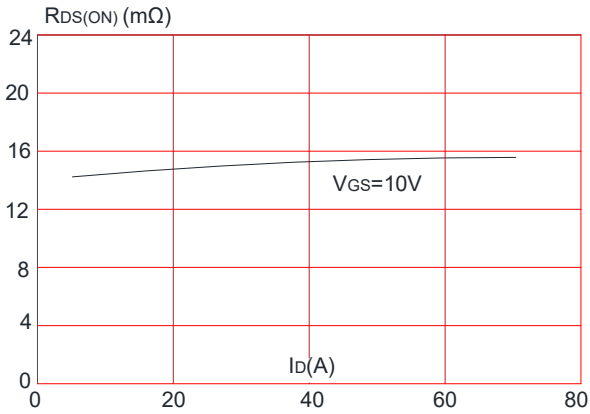


Figure 4: Body Diode Characteristics

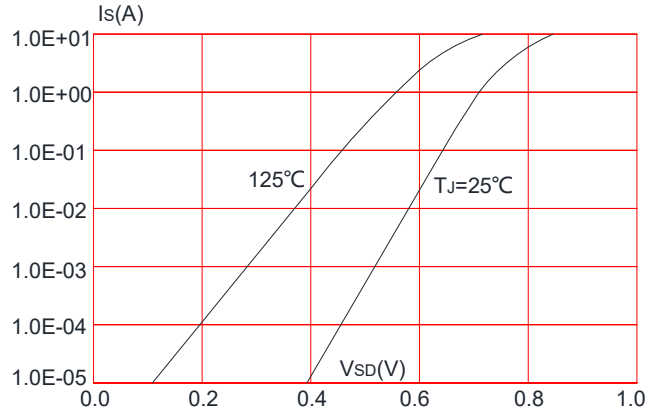


Figure 5: Gate Charge Characteristics

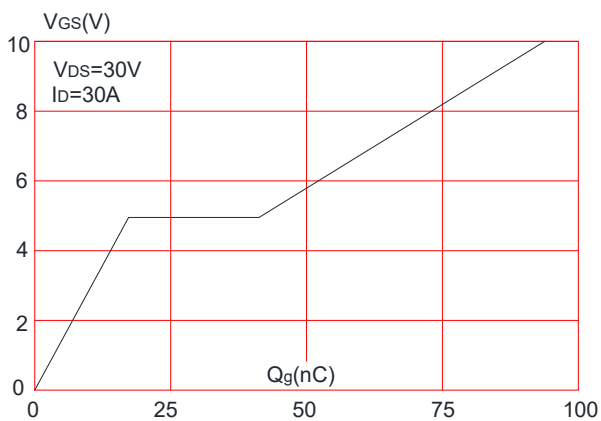
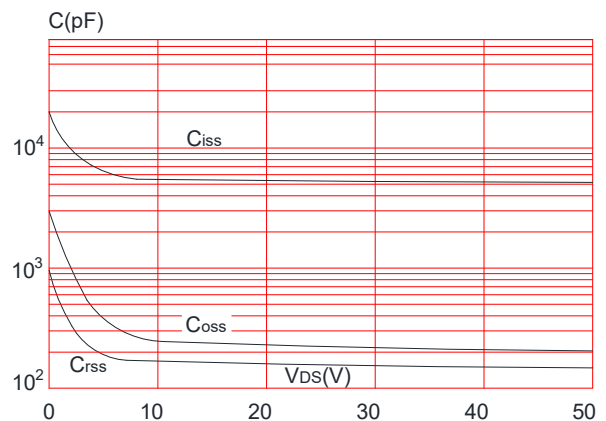


Figure 6: Capacitance Characteristics





JMTK170N10A

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

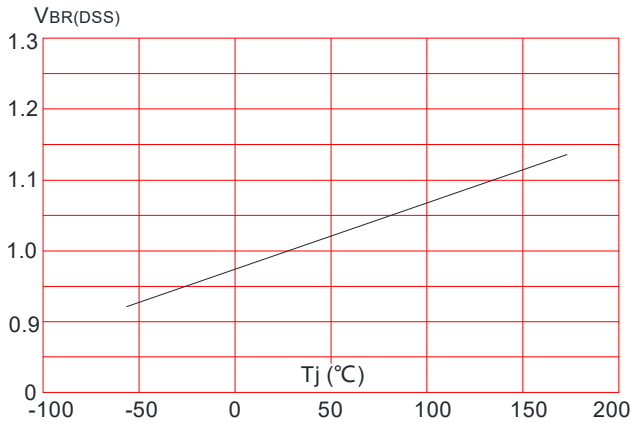


Figure 8: Normalized on Resistance vs. Junction Temperature

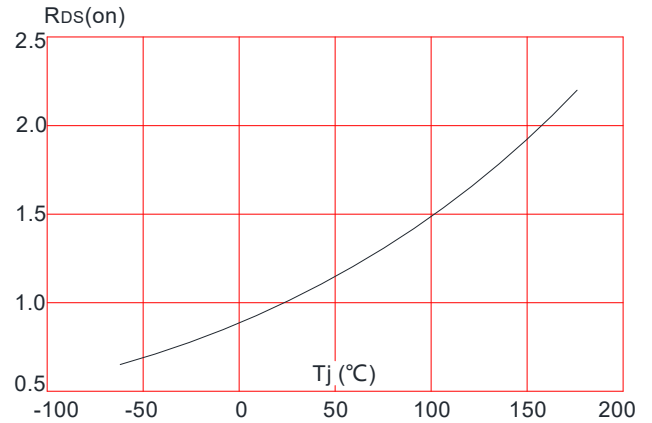


Figure 9: Maximum Safe Operating Area

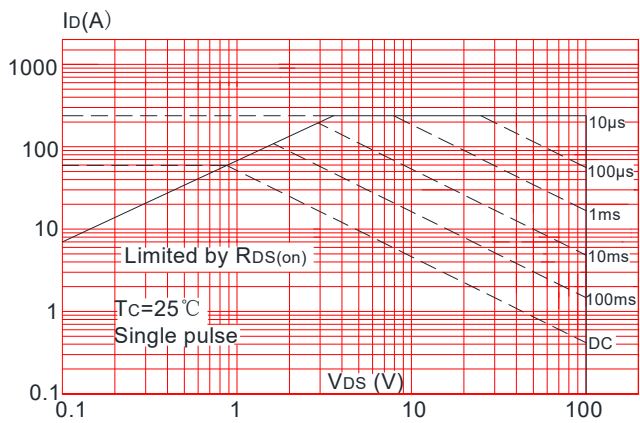


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

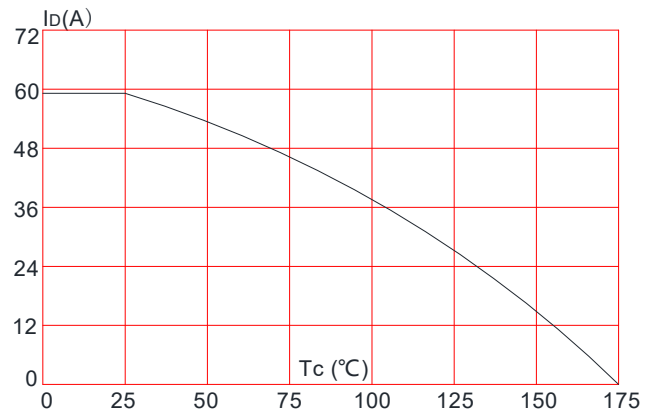
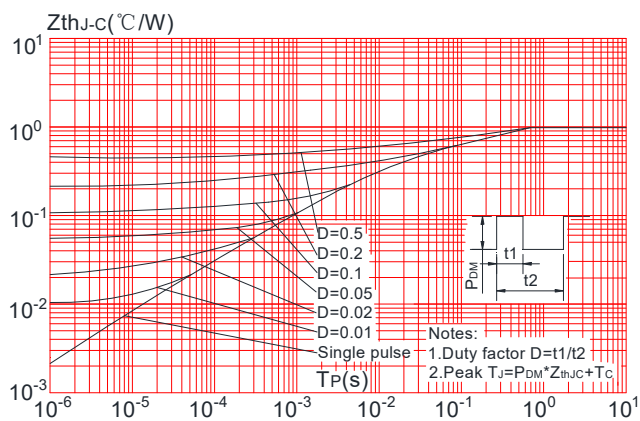


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

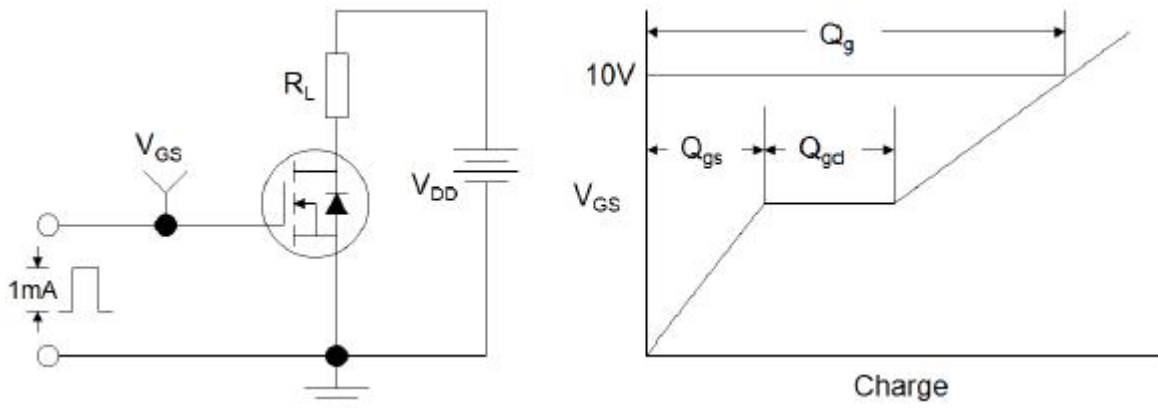


Figure1:Gate Charge Test Circuit & Waveform

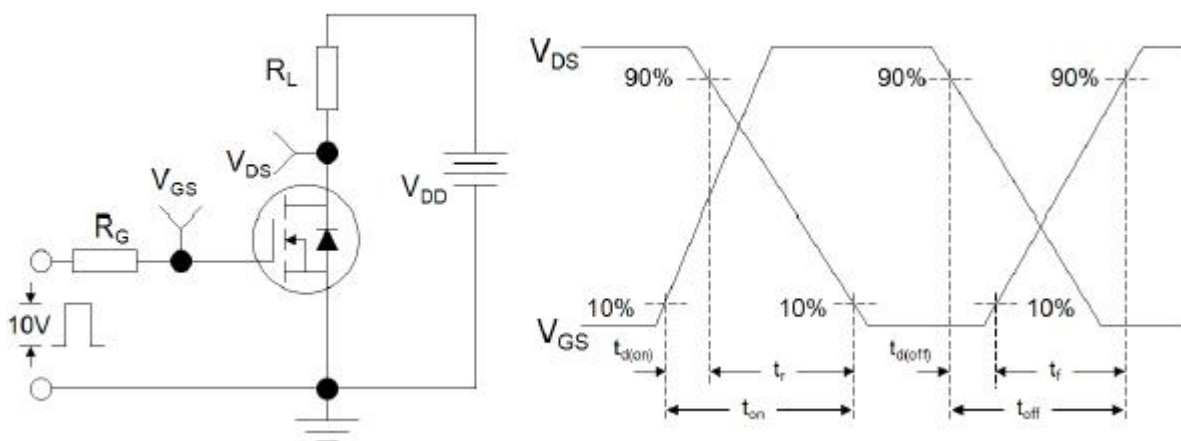


Figure 2: Resistive Switching Test Circuit & Waveforms

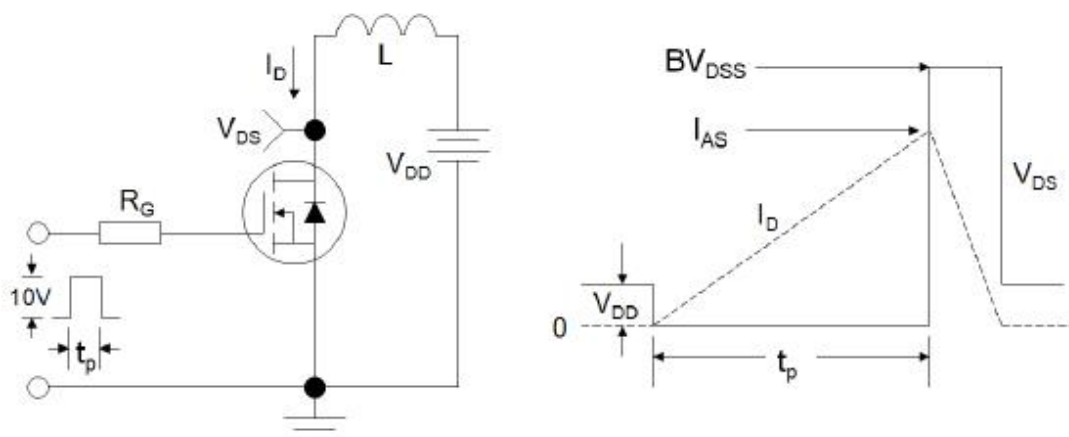
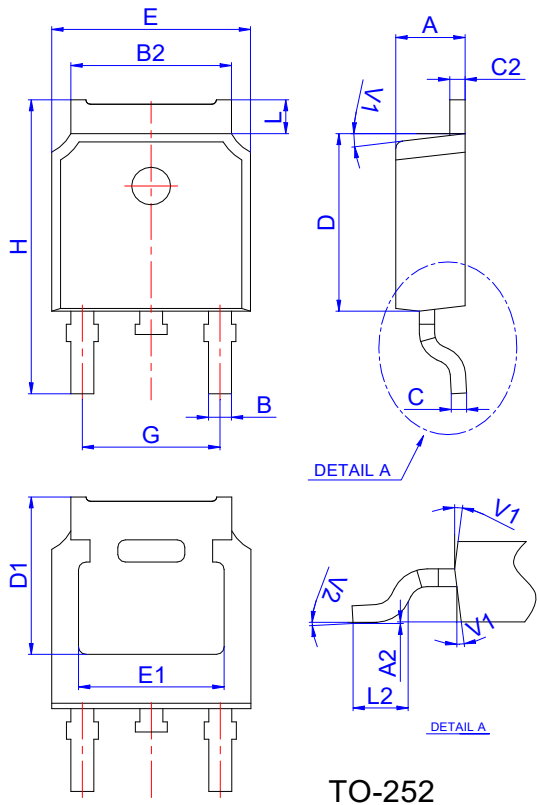


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

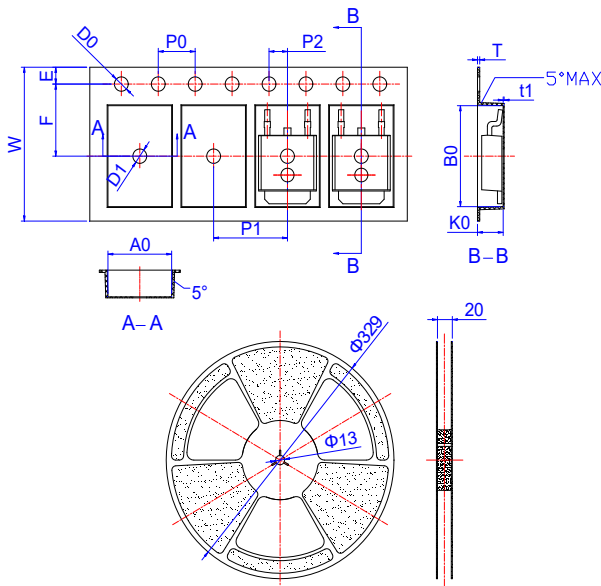


Package Mechanical Data-TO-252-4R



| Ref. | Dimensions | | | | | |
|------|-------------|------|-------|----------|------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 2.10 | | 2.50 | 0.083 | | 0.098 |
| A2 | 0 | | 0.10 | 0 | | 0.004 |
| B | 0.66 | | 0.86 | 0.026 | | 0.034 |
| B2 | 5.18 | | 5.48 | 0.202 | | 0.216 |
| C | 0.40 | | 0.60 | 0.016 | | 0.024 |
| C2 | 0.44 | | 0.58 | 0.017 | | 0.023 |
| D | 5.90 | | 6.30 | 0.232 | | 0.248 |
| D1 | 5.30REF | | | 0.209REF | | |
| E | 6.40 | | 6.80 | 0.252 | | 0.268 |
| E1 | 4.63 | | | 0.182 | | |
| G | 4.47 | | 4.67 | 0.176 | | 0.184 |
| H | 9.50 | | 10.70 | 0.374 | | 0.421 |
| L | 1.09 | | 1.21 | 0.043 | | 0.048 |
| L2 | 1.35 | | 1.65 | 0.053 | | 0.065 |
| V1 | | 7° | | | 7° | |
| V2 | 0° | | 6° | 0° | | 6° |

Reel Specification-TO-252-4R




| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| W | 15.90 | 16.00 | 16.10 | 0.626 | 0.630 | 0.634 |
| E | 1.65 | 1.75 | 1.85 | 0.065 | 0.069 | 0.073 |
| F | 7.40 | 7.50 | 7.60 | 0.291 | 0.295 | 0.299 |
| D0 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| D1 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 |
| P0 | 3.90 | 4.00 | 4.10 | 0.154 | 0.157 | 0.161 |
| P1 | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| P2 | 1.90 | 2.00 | 2.10 | 0.075 | 0.079 | 0.083 |
| A0 | 6.85 | 6.90 | 7.00 | 0.270 | 0.271 | 0.276 |
| B0 | 10.45 | 10.50 | 10.60 | 0.411 | 0.413 | 0.417 |
| K0 | 2.68 | 2.78 | 2.88 | 0.105 | 0.109 | 0.113 |
| T | 0.24 | | 0.27 | 0.009 | | 0.011 |
| t1 | 0.10 | | | 0.004 | | |
| 10P0 | 39.80 | 40.00 | 40.20 | 1.567 | 1.575 | 1.583 |



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